

# Field S op T ench IGBT

## 40 A, 650 V

# AFGHL40T65SQ

Using the novel field stop 4th generation high speed IGBT technology. AFGHL40T65SQ which is AEC Q101 qualified offers the optimum performance for both hard and soft switching topology in automotive application. It is a stand—alone IGBT.

#### **Features**

- AEC-Q101 Qualified
- Maximum Junction Temperature: T<sub>J</sub> = 175°C
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: V<sub>CE(Sat)</sub> = 1.6 V (Typ.) @ I<sub>C</sub> = 40 A
- 100% of the Parts are Tested for I<sub>LM</sub> (Note 2)
- Fast Switching
- Tight Parameter Distribution
- RoHS Compliant

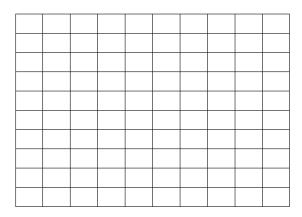
GateToEmitter Voltage
Transient Gate-to-Emitter Voltage

	V <sub>GES</sub>	±20 ±30	V
Collector Current (Note 1)	I <sub>C</sub>	80 40	Α
Pulsed Collector Current (Note 2)	I <sub>LM</sub>	160	Α
Pulsed Collector Current (Note 3)	I <sub>CM</sub>	160	Α
Maximum Power Dissipation @ $T_C = 25^{\circ}C$ @ $T_C = 100^{\circ}C$	P <sub>D</sub>	239 119	W
Operating Junction / Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	–55 to +175	°C

#### THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT			

#### **TYPICAL CHARACTERISTICS**



**Figure 1. Typical Output Characteristics** 

**Figure 2. Typical Output Characteristics** 

Figure 3. Typical Saturation Voltage

Figure 4. Saturation Voltage vs. Case Temperature

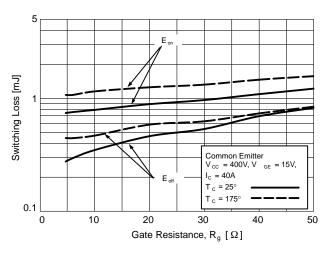
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Figure 5. Saturation Voltage vs. V<sub>GE</sub>

Figure 6. Saturation Voltage vs. V<sub>GE</sub>

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## **TYPICAL CHARACTERISTICS**



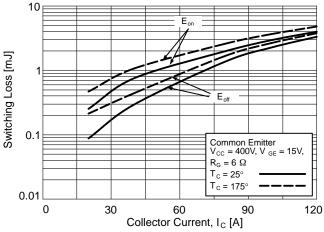


Figure 13. Switching Loss vs. Gate Resistance

Figure 14. Switching Loss vs. Collector Current

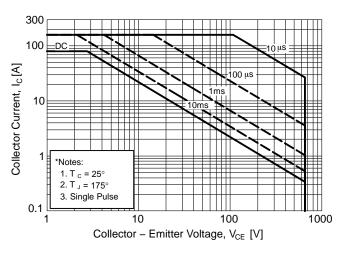


Figure 15. SOA Characteristics

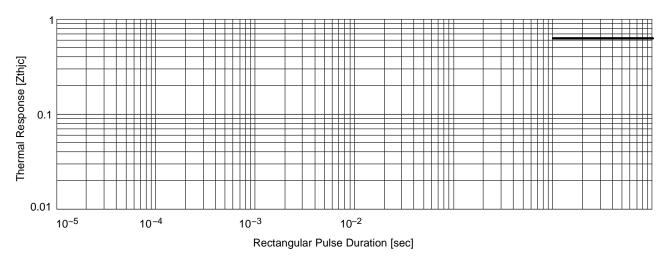


Figure 16. transient Thermal Impedance of IGBT

